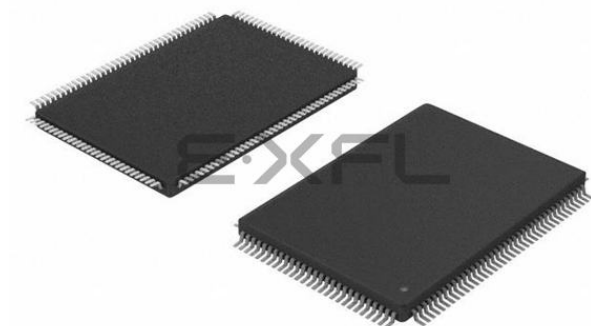


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Details

Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I ² C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	111
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	31K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	128-LQFP
Supplier Device Package	128-LFQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30627fhpgp-u3c

Table 1.5 Product List (2) (M16C/62P)

As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type ⁽¹⁾	Remarks
M30622MHP-XXXFP	384 Kbytes	16 Kbytes	PRQP0100JB-A	Mask ROM version
M30622MHP-XXXGP			PLQP0100KB-A	
M30623MHP-XXXGP			PLQP0128KB-A	
M30624MHP-XXXFP		24 Kbytes	PRQP0100JB-A	
M30624MHP-XXXGP			PLQP0100KB-A	
M30625MHP-XXXGP			PLQP0128KB-A	
M30626MHP-XXXFP		31 Kbytes	PRQP0100JB-A	
M30626MHP-XXXGP			PLQP0100KB-A	
M30627MHP-XXXGP			PLQP0128KB-A	
M30626MJP-XXXFP (D)	512 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626MJP-XXXGP (D)			PLQP0100KB-A	
M30627MJP-XXXGP (D)			PLQP0128KB-A	
M30622F8PFP	64K+4 Kbytes	4 Kbytes	PRQP0100JB-A	Flash memory version ⁽²⁾
M30622F8PGP			PLQP0100KB-A	
M30623F8PGP			PRQP0080JA-A	
M30620FCPFP	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A	
M30620FCPGP			PLQP0100KB-A	
M30621FCPGP			PRQP0080JA-A	
M3062LFGPFP ⁽³⁾ (D)	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	
M3062LFGPGP ⁽³⁾ (D)			PLQP0100KB-A	
M30625FGPGP			PLQP0128KB-A	
M30626FHPFP	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FHPPGP			PLQP0100KB-A	
M30627FHPPGP			PLQP0128KB-A	
M30626FJPFP	512K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FJPPGP			PLQP0100KB-A	
M30627FJPPGP			PLQP0128KB-A	
M30622SPFP	–	4 Kbytes	PRQP0100JB-A	ROM-less version
M30622SPGP			PLQP0100KB-A	
M30620SPFP		10 Kbytes	PRQP0100JB-A	
M30620SPGP			PLQP0100KB-A	
M30624SPFP (D)	–	20 Kbytes	PRQP0100JB-A	
M30624SPGP (D)			PLQP0100KB-A	
M30626SPFP (D)		31 Kbytes	PRQP0100JB-A	
M30626SPGP (D)			PLQP0100KB-A	

(D): Under development

NOTES:

- The old package type numbers of each package type are as follows.
 PLQP0128KB-A : 128P6Q-A,
 PRQP0100JB-A : 100P6S-A,
 PLQP0100KB-A : 100P6Q-A,
 PRQP0080JA-A : 80P6S-A
- In the flash memory version, there is 4K bytes area (block A).
- Please use M3062LFGPFP and M3062LFGPGP for your new system instead of M30624FGPFP and M30624FGPGP. The M16C/62P Group (M16C/62P, M16C/62PT) hardware manual is still good for M30624FGPFP and M30624FGPGP.

M30624FGPFP	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	Flash memory version
M30624FGPGP			PLQP0100KB-A	

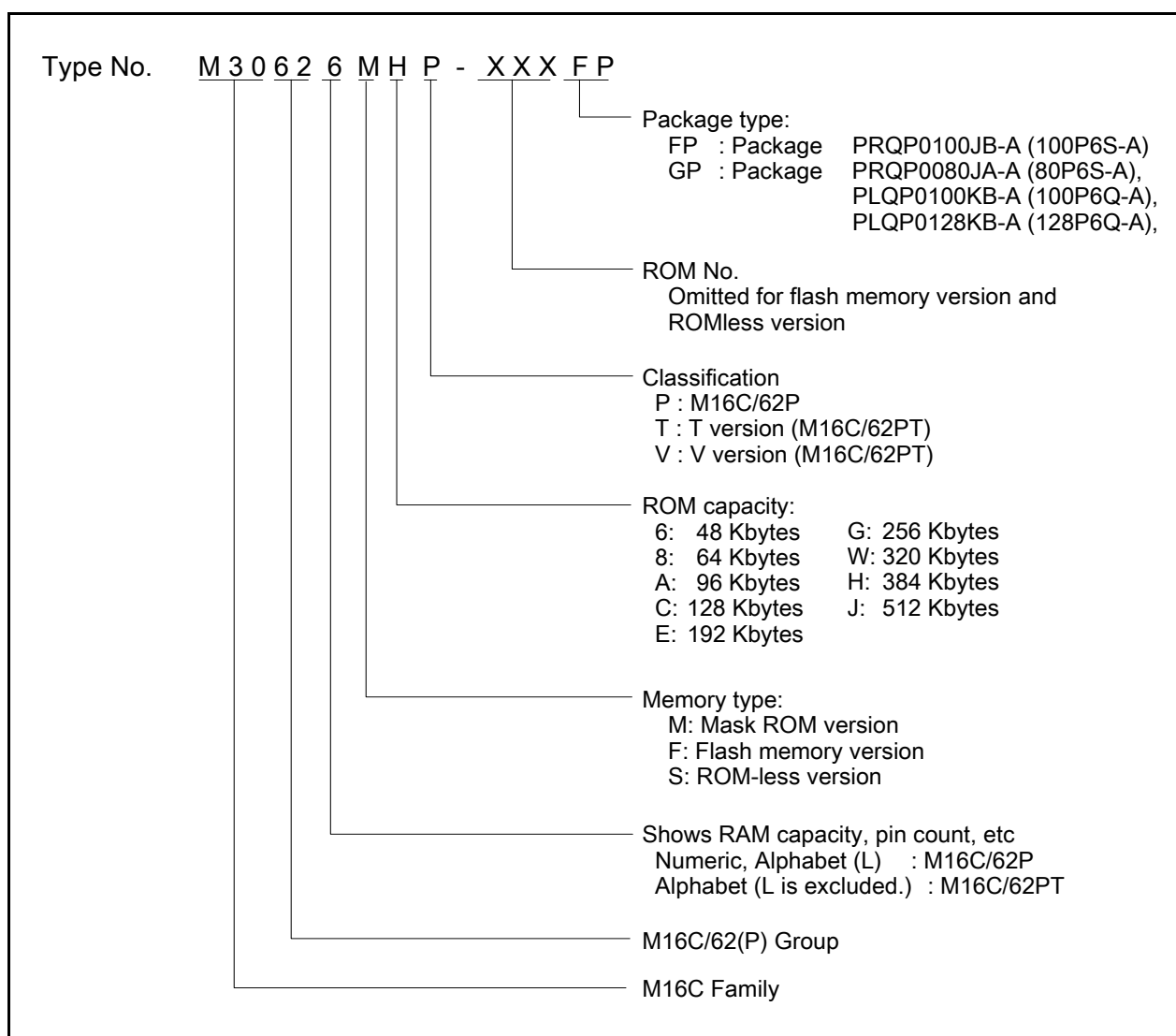


Figure 1.3 Type No., Memory Size, and Package

Table 1.10 Pin Characteristics for 128-Pin Package (1)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
1	VREF						
2	AVCC						
3		P9_7			SIN4	ADTRG	
4		P9_6			SOUT4	ANEX1	
5		P9_5			CLK4	ANEX0	
6		P9_4		TB4IN		DA1	
7		P9_3		TB3IN		DA0	
8		P9_2		TB2IN	SOUT3		
9		P9_1		TB1IN	SIN3		
10		P9_0		TB0IN	CLK3		
11		P14_1					
12		P14_0					
13	BYTE						
14	CNVSS						
15	XCIN	P8_7					
16	XCOUT	P8_6					
17	RESET						
18	XOUT						
19	VSS						
20	XIN						
21	VCC1						
22		P8_5	NMI				
23		P8_4	INT2	ZP			
24		P8_3	INT1				
25		P8_2	INT0				
26		P8_1		TA4IN/U			
27		P8_0		TA4OUT/U			
28		P7_7		TA3IN			
29		P7_6		TA3OUT			
30		P7_5		TA2IN/W			
31		P7_4		TA2OUT/W			
32		P7_3		TA1IN/V	CTS2/RTS2		
33		P7_2		TA1OUT/V	CLK2		
34		P7_1		TA0IN/TB5IN	RXD2/SCL2		
35		P7_0		TA0OUT	TXD2/SDA2		
36		P6_7			TXD1/SDA1		
37	VCC1						
38		P6_6			RXD1/SCL1		
39	VSS						
40		P6_5			CLK1		
41		P6_4			CTS1/RTS1/CTS0/CLKS1		
42		P6_3			TXD0/SDA0		
43		P6_2			RXD0/SCL0		
44		P6_1			CLK0		
45		P6_0			CTS0/RTS0		
46		P13_7					
47		P13_6					
48		P13_5					
49		P13_4					
50		P5_7					RDY/CLKOUT

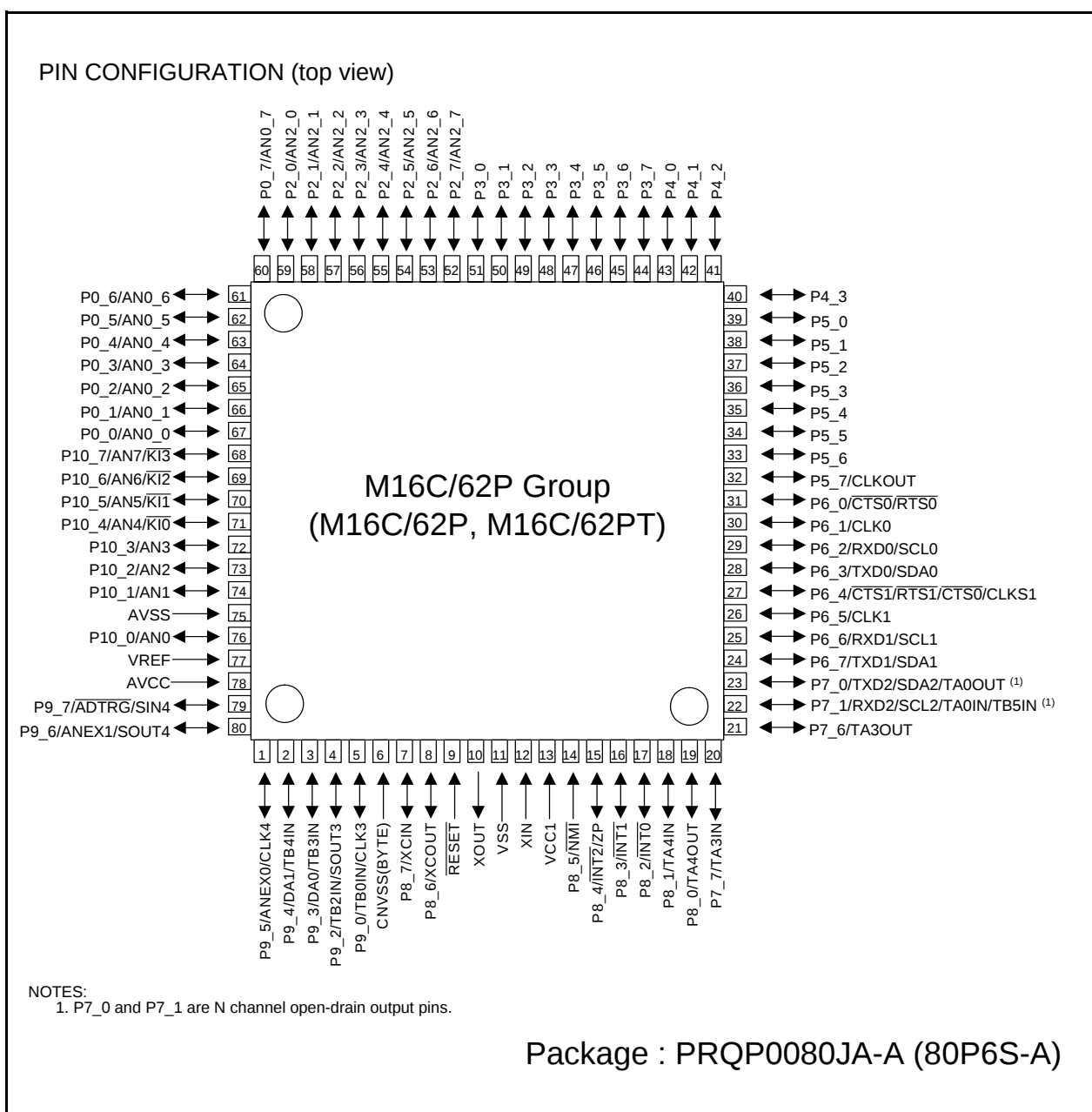


Figure 1.9 Pin Configuration (Top View)

Table 1.16 Pin Characteristics for 80-Pin Package (2)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
51		P3_0					
52		P2_7				AN2_7	
53		P2_6				AN2_6	
54		P2_5				AN2_5	
55		P2_4				AN2_4	
56		P2_3				AN2_3	
57		P2_2				AN2_2	
58		P2_1				AN2_1	
59		P2_0				AN2_0	
60		P0_7				AN0_7	
61		P0_6				AN0_6	
62		P0_5				AN0_5	
63		P0_4				AN0_4	
64		P0_3				AN0_3	
65		P0_2				AN0_2	
66		P0_1				AN0_1	
67		P0_0				AN0_0	
68		P10_7	KI3			AN7	
69		P10_6	KI2			AN6	
70		P10_5	KI1			AN5	
71		P10_4	KI0			AN4	
72		P10_3				AN3	
73		P10_2				AN2	
74		P10_1				AN1	
75	AVSS						
76		P10_0				AN0	
77	VREF						
78	AVCC						
79		P9_7			SIN4	ADTRG	
80		P9_6			SOUT4	ANEX1	

3. Memory

Figure 3.1 is a Memory Map of the M16C/62P group. The address space extends the 1M bytes from address 00000h to FFFFFh.

The internal ROM is allocated in a lower address direction beginning with address FFFFFh. For example, a 64-Kbyte internal ROM is allocated to the addresses from F0000h to FFFFFh.

As for the flash memory version, 4-Kbyte space (block A) exists in 0F000h to 0FFFFh. 4-Kbyte space is mainly for storing data. In addition to storing data, 4-Kbyte space also can store programs.

The fixed interrupt vector table is allocated to the addresses from FFFDCh to FFFFFh. Therefore, store the start address of each interrupt routine here.

The internal RAM is allocated in an upper address direction beginning with address 00400h. For example, a 10-Kbyte internal RAM is allocated to the addresses from 00400h to 02BFFh. In addition to storing data, the internal RAM also stores the stack used when calling subroutines and when interrupts are generated.

The SRF is allocated to the addresses from 00000h to 003FFh. Peripheral function control registers are located here. Of the SFR, any area which has no functions allocated is reserved for future use and cannot be used by users.

The special page vector table is allocated to the addresses from FFE00h to FFFDBh. This vector is used by the JMPS or JSRS instruction. For details, refer to the **M16C/60 and M16C/20 Series Software Manual**.

In memory expansion and microprocessor modes, some areas are reserved for future use and cannot be used by users. Use M16C/62P (80-pin version) and M16C/62PT in single-chip mode. The memory expansion and microprocessor modes cannot be used

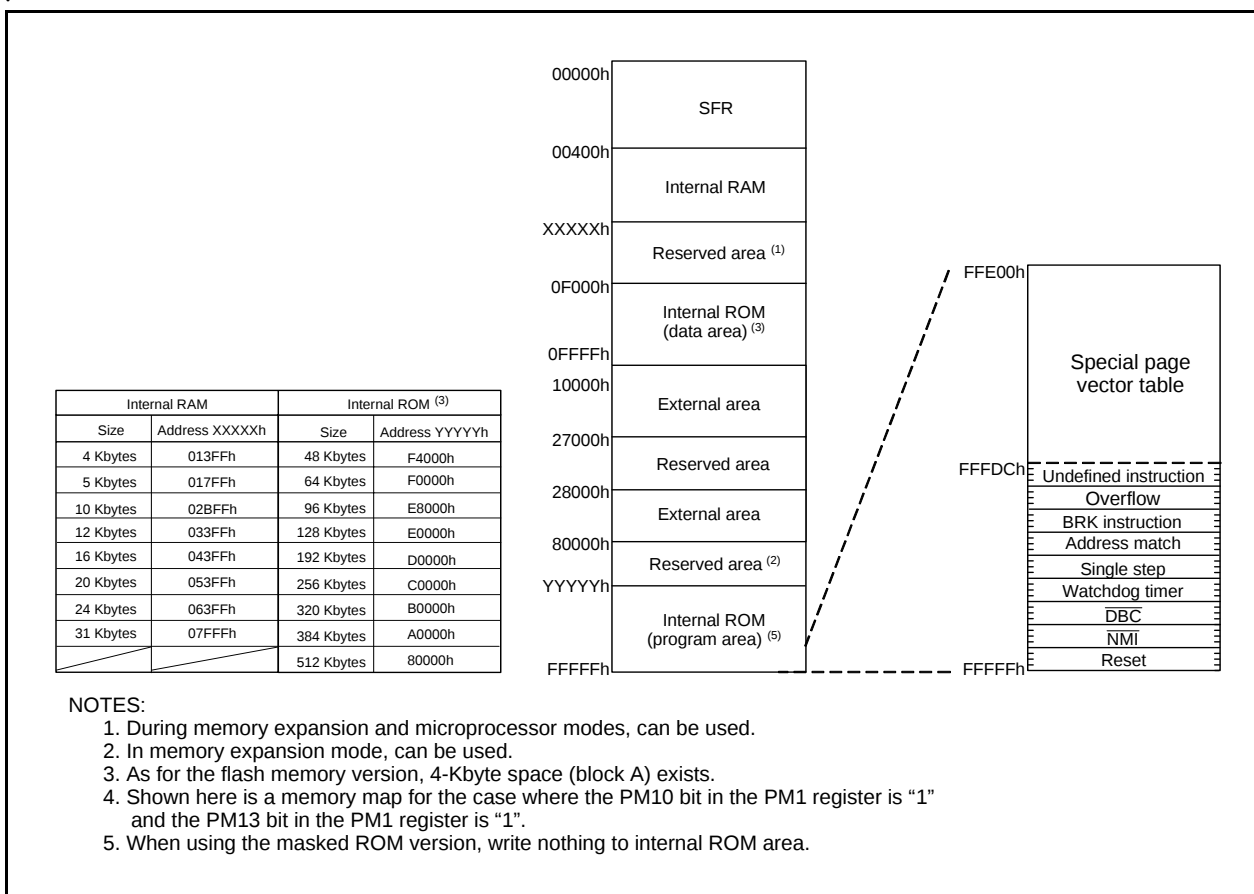


Figure 3.1 Memory Map

Table 4.2 SFR Information (2) ⁽¹⁾

Address	Register	Symbol	After Reset
0040h			
0041h			
0042h			
0043h			
0044h	INT3 Interrupt Control Register	INT3IC	XX00X000b
0045h	Timer B5 Interrupt Control Register	TB5IC	XXXXX000b
0046h	Timer B4 Interrupt Control Register, UART1 BUS Collision Detection Interrupt Control Register	TB4IC, U1BCNIC	XXXXX000b
0047h	Timer B3 Interrupt Control Register, UART0 BUS Collision Detection Interrupt Control Register	TB3IC, U0BCNIC	XXXXX000b
0048h	SI/O4 Interrupt Control Register, INT5 Interrupt Control Register	S4IC, INT5IC	XX00X000b
0049h	SI/O3 Interrupt Control Register, INT4 Interrupt Control Register	S3IC, INT4IC	XX00X000b
004Ah	UART2 Bus Collision Detection Interrupt Control Register	BCNIC	XXXXX000b
004Bh	DMA0 Interrupt Control Register	DM0IC	XXXXX000b
004Ch	DMA1 Interrupt Control Register	DM1IC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
0050h	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	Timer A0 Interrupt Control Register	TA0IC	XXXXX000b
0056h	Timer A1 Interrupt Control Register	TA1IC	XXXXX000b
0057h	Timer A2 Interrupt Control Register	TA2IC	XXXXX000b
0058h	Timer A3 Interrupt Control Register	TA3IC	XXXXX000b
0059h	Timer A4 Interrupt Control Register	TA4IC	XXXXX000b
005Ah	Timer B0 Interrupt Control Register	TB0IC	XXXXX000b
005Bh	Timer B1 Interrupt Control Register	TB1IC	XXXXX000b
005Ch	Timer B2 Interrupt Control Register	TB2IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Fh	INT2 Interrupt Control Register	INT2IC	XX00X000b
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

NOTES:

1. The blank areas are reserved and cannot be accessed by users.

X : Nothing is mapped to this bit

Table 5.4 A/D Conversion Characteristics (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		VREF=VCC1				10	Bits
INL	Integral Non-Linearity Error	10bit	VREF=VCC1=5V	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±3	LSB
				External operation amp connection mode			±7	LSB
			VREF=VCC1=3.3V	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±5	LSB
				External operation amp connection mode			±7	LSB
		8bit	VREF=VCC1=5V, 3.3V				±2	LSB
		–	Absolute Accuracy	10bit	VREF=VCC1=5V	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input		
External operation amp connection mode						±7	LSB	
VREF=VCC1=3.3V	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input					±5	LSB	
	External operation amp connection mode					±7	LSB	
8bit	VREF=VCC1=5V, 3.3V					±2	LSB	
–	Tolerance Level Impedance						3	
DNL	Differential Non-Linearity Error						±1	LSB
–	Offset Error						±3	LSB
–	Gain Error						±3	LSB
RLADDER	Ladder Resistance		VREF=VCC1		10		40	kΩ
tCONV	10-bit Conversion Time, Sample & Hold Available		VREF=VCC1=5V, φAD=12MHz		2.75			μs
tCONV	8-bit Conversion Time, Sample & Hold Available		VREF=VCC1=5V, φAD=12MHz		2.33			μs
tsAMP	Sampling Time				0.25			μs
VREF	Reference Voltage				2.0		VCC1	V
VIA	Analog Input Voltage				0		VREF	V

NOTES:

1. Referenced to VCC1=AVCC=VREF=3.3 to 5.5V, VSS=AVSS=0V at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified.
2. If VCC1 > VCC2, do not use AN0_0 to AN0_7 and AN2_0 to AN2_7 as analog input pins.
3. φAD frequency must be 12 MHz or less. And divide the fAD if VCC1 is less than 4.0V, and φAD frequency into 10 MHz or less.
4. When sample & hold is disabled, φAD frequency must be 250 kHz or more, in addition to the limitation in Note 3.
When sample & hold is enabled, φAD frequency must be 1MHz or more, in addition to the limitation in Note 3.

Table 5.5 D/A Conversion Characteristics ⁽¹⁾

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution				8	Bits
–	Absolute Accuracy				1.0	%
t _{su}	Setup Time				3	μs
R _o	Output Resistance		4	10	20	kΩ
I _{VREF}	Reference Power Supply Input Current	(NOTE 2)			1.5	mA

NOTES:

1. Referenced to V_{CC1}=V_{REF}=3.3 to 5.5V, V_{SS}=AV_{SS}=0V at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified.
2. This applies when using one D/A converter, with the D/A register for the unused D/A converter set to “00h”. The resistor ladder of the A/D converter is not included. Also, when D/A register contents are not “00h”, the I_{VREF} will flow even if V_{ref} is disconnected by the A/D control register.

Table 5.9 Low Voltage Detection Circuit Electrical Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det4}	Low Voltage Detection Voltage ⁽¹⁾	V _{CC1} =0.8V to 5.5V	3.3	3.8	4.4	V
V _{det3}	Reset Level Detection Voltage ^(1, 2)		2.2	2.8	3.6	V
V _{det4} -V _{det3}	Electric potential difference of Low Voltage Detection and Reset Level Detection		0.3			V
V _{det3s}	Low Voltage Reset Retention Voltage				0.8	V
V _{det3r}	Low Voltage Reset Release Voltage ⁽³⁾		2.2	2.9	4.0	V

NOTES:

1. V_{det4} > V_{det3}.
2. Where reset level detection voltage is less than 2.7 V, if the supply power voltage is greater than the reset level detection voltage, the microcomputer operates with f(BCLK) ≤ 10MHz.
3. V_{det3r} > V_{det3} is not guaranteed.
4. The voltage detection circuit is designed to use when V_{CC1} is set to 5V.

Table 5.10 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
t _d (P-R)	Time for Internal Power Supply Stabilization During Powering-On	V _{CC1} =2.7V to 5.5V			2	ms
t _d (R-S)	STOP Release Time				150	μs
t _d (W-S)	Low Power Dissipation Mode Wait Mode Release Time				150	μs
t _d (S-R)	Brown-out Detection Reset (Hardware Reset 2) Release Wait Time	V _{CC1} =V _{det3r} to 5.5V		6 ⁽¹⁾	20	ms
t _d (E-A)	Low Voltage Detection Circuit Operation Start Time	V _{CC1} =2.7V to 5.5V			20	μs

NOTES:

1. When V_{CC1} = 5V.

$$V_{CC1}=V_{CC2}=5V$$

Table 5.11 Electrical Characteristics (1) (1)

Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
VOH	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	IOH=−5mA	VCC1−2.0		VCC1	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOH=−5mA (2)	VCC2−2.0		VCC2	
VOH	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	OH=−200μA	VCC1−0.3		VCC1	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOH=−200μA (2)	VCC2−0.3		VCC2	
VOH	HIGH Output Voltage XOUT	HIGHPOWER	IOH=−1mA	VCC1−2.0		VCC1	V
		LOWPOWER	IOH=−0.5mA	VCC1−2.0		VCC1	
	HIGH Output Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
		LOWPOWER	With no load applied		1.6		
VOL	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	IOL=5mA			2.0	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOL=5mA (2)			2.0	
VOL	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	IOL=200μA			0.45	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOL=200μA (2)			0.45	
VOL	LOW Output Voltage XOUT	HIGHPOWER	IOL=1mA			2.0	V
		LOWPOWER	IOL=0.5mA			2.0	
	LOW Output Voltage XCOUT	HIGHPOWER	With no load applied		0		V
		LOWPOWER	With no load applied		0		
VT+−VT−	Hysteresis	HOLD, RDY, TA0IN to TA4IN, TB0IN to TB5IN, INT0 to INT5, NMI, ADTRG, CTS0 to CTS2, CLK0 to CLK4, TA0OUT to TA4OUT, KI0 to KI3, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4		0.2		1.0	V
VT+−VT−	Hysteresis	RESET		0.2		2.5	V
IiH	HIGH Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	Vi=5V			5.0	μA
IiL	LOW Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	Vi=0V			−5.0	μA
RPULLUP	Pull-Up Resistance (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1	Vi=0V	30	50	170	kΩ
RtXIN	Feedback Resistance XIN				1.5		MΩ
RtXCIN	Feedback Resistance XCIN				15		MΩ
VRAM	RAM Retention Voltage		At stop mode	2.0			V

NOTES:

1. Referenced to VCC1=VCC2=4.2 to 5.5V, VSS = 0V at Topr = −20 to 85°C / −40 to 85°C, f(BCLK)=24MHz unless otherwise specified.
2. Where the product is used at VCC1 = 5 V and VCC2 = 3 V, refer to the 3 V version value for the pin specified value on VCC2 port side.
3. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

$$V_{CC1}=V_{CC2}=5V$$

Timing Requirements

($V_{CC1} = V_{CC2} = 5V$, $V_{SS} = 0V$, at $T_{opr} = -20$ to $85^{\circ}C$ / -40 to $85^{\circ}C$ unless otherwise specified)

Table 5.21 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	100		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	40		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	40		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	200		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	80		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	80		ns

Table 5.22 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.23 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.24 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{ADTRG}$ Input Cycle Time	1000		ns
$t_{w(ADL)}$	$\overline{ADTRG}$ input LOW Pulse Width	125		ns

Table 5.25 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	200		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	100		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	100		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		80	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	70		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

Table 5.26 External Interrupt $\overline{INTi}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ Input HIGH Pulse Width	250		ns
$t_{w(INL)}$	$\overline{INTi}$ Input LOW Pulse Width	250		ns

$$V_{CC1}=V_{CC2}=5V$$

Switching Characteristics

($V_{CC1} = V_{CC2} = 5V$, $V_{SS} = 0V$, at $T_{opr} = -20$ to $85^{\circ}C$ / -40 to $85^{\circ}C$ unless otherwise specified)

Table 5.27 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_d(BCLK-AD)$	Address Output Delay Time	See Figure 5.2		25	ns
$t_h(BCLK-AD)$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_h(RD-AD)$	Address Output Hold Time (in relation to RD)		0		ns
$t_h(WR-AD)$	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
$t_d(BCLK-CS)$	Chip Select Output Delay Time			25	ns
$t_h(BCLK-CS)$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_d(BCLK-ALE)$	ALE Signal Output Delay Time			15	ns
$t_h(BCLK-ALE)$	ALE Signal Output Hold Time		-4		ns
$t_d(BCLK-RD)$	RD Signal Output Delay Time			25	ns
$t_h(BCLK-RD)$	RD Signal Output Hold Time		0		ns
$t_d(BCLK-WR)$	WR Signal Output Delay Time			25	ns
$t_h(BCLK-WR)$	WR Signal Output Hold Time		0		ns
$t_d(BCLK-DB)$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_h(BCLK-DB)$	Data Output Hold Time (in relation to BCLK) ⁽³⁾		4		ns
$t_d(DB-WR)$	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
$t_h(WR-DB)$	Data Output Hold Time (in relation to WR) ⁽³⁾		(NOTE 2)		ns
$t_d(BCLK-HLDA)$	HLDA Output Delay Time			40	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 40 [ns] \quad f(BCLK) \text{ is } 12.5MHz \text{ or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10 [ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.

Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.

Hold time of data bus is expressed in

$$t = -CR \times \ln(1 - V_{OL} / V_{CC2})$$

by a circuit of the right figure.

For example, when $V_{OL} = 0.2V_{CC2}$, $C = 30pF$, $R = 1k\Omega$, hold time of output "L" level is

$$t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2}) = 6.7ns.$$

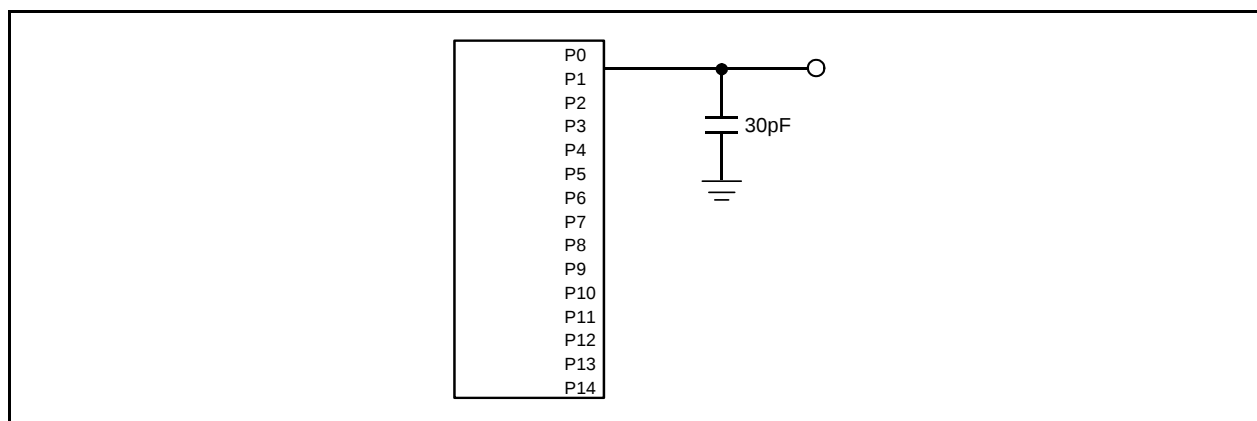
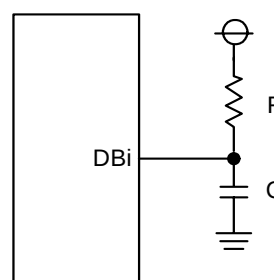


Figure 5.2 Ports P0 to P14 Measurement Circuit

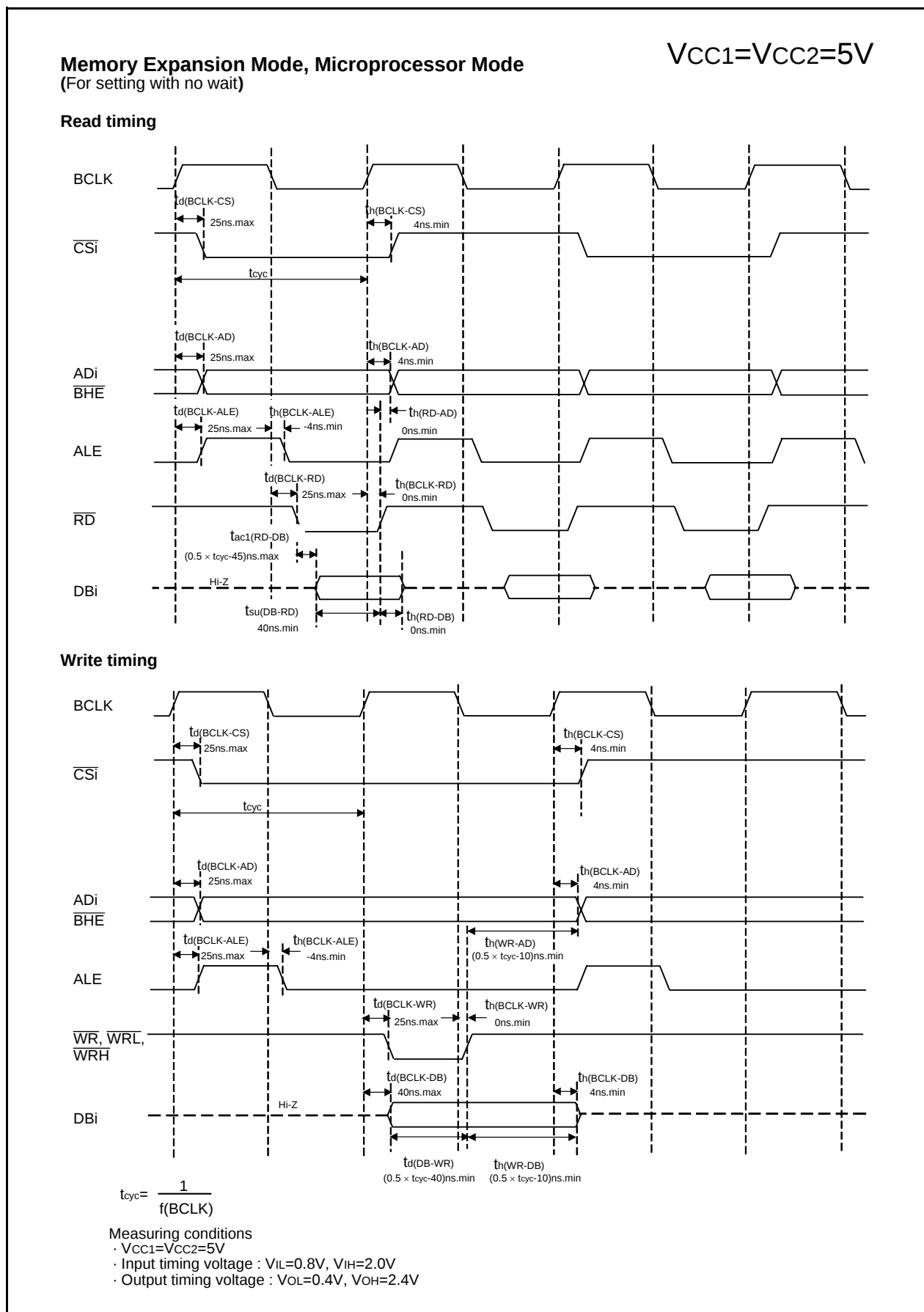


Figure 5.6 Timing Diagram (4)

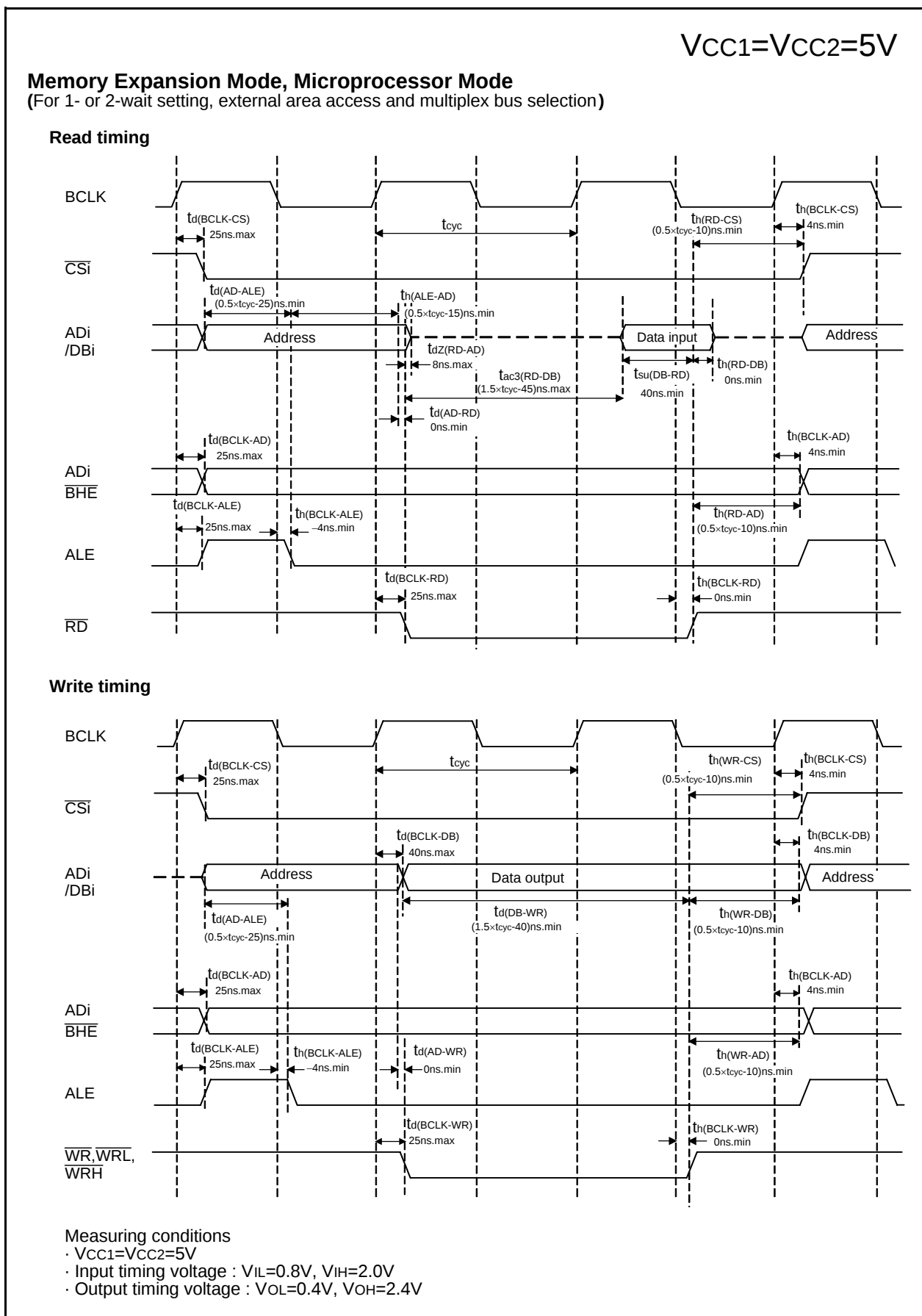


Figure 5.10 Timing Diagram (8)

$$V_{CC1}=V_{CC2}=3V$$

Table 5.30 Electrical Characteristics (1) (1)

Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
VOH	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	IOH=−1mA	VCC1−0.5		VCC1	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOH=−1mA (2)	VCC2−0.5		VCC2	
VOH	HIGH Output Voltage XOUT	HIGHPOWER	IOH=−0.1mA	VCC1−0.5		VCC1	V
		LOWPOWER	IOH=−50μA	VCC1−0.5		VCC1	
	HIGH Output Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
		LOWPOWER	With no load applied		1.6		
VOL	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	IOL=1mA			0.5	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOL=1mA (2)			0.5	
VOL	LOW Output Voltage XOUT	HIGHPOWER	IOL=0.1mA			0.5	V
		LOWPOWER	IOL=50μA			0.5	
	LOW Output Voltage XCOUT	HIGHPOWER	With no load applied		0		V
		LOWPOWER	With no load applied		0		
VT+−VT−	Hysteresis	HOLD, RDY, TA0IN to TA4IN, TBOIN to TB5IN, INT0 to INT5, NMI, ADTRG, CTS0 to CTS2, CLK0 to CLK4, TA0OUT to TA4OUT, KI0 to KI3, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4		0.2		0.8	V
VT+−VT−	Hysteresis	RESET		0.2	(0.7)	1.8	V
IiH	HIGH Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	VI=3V			4.0	μA
IiL	LOW Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	VI=0V			−4.0	μA
RPULLUP	Pull-Up Resistance (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1	VI=0V	50	100	500	kΩ
RfXIN	Feedback Resistance XIN				3.0		MΩ
RfXCIN	Feedback Resistance XCIN				25		MΩ
VRAM	RAM Retention Voltage		At stop mode	2.0			V

NOTES:

1. Referenced to VCC1 = VCC2 = 2.7 to 3.3V, VSS = 0V at Topr = −20 to 85°C / −40 to 85°C, f(XIN)=10MHz no wait unless otherwise specified.
2. VCC1 for the port P6 to P11 and P14, and VCC2 for the port P0 to P5 and P12 to P13
3. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

Table 5.31 Electrical Characteristics (2) ⁽¹⁾

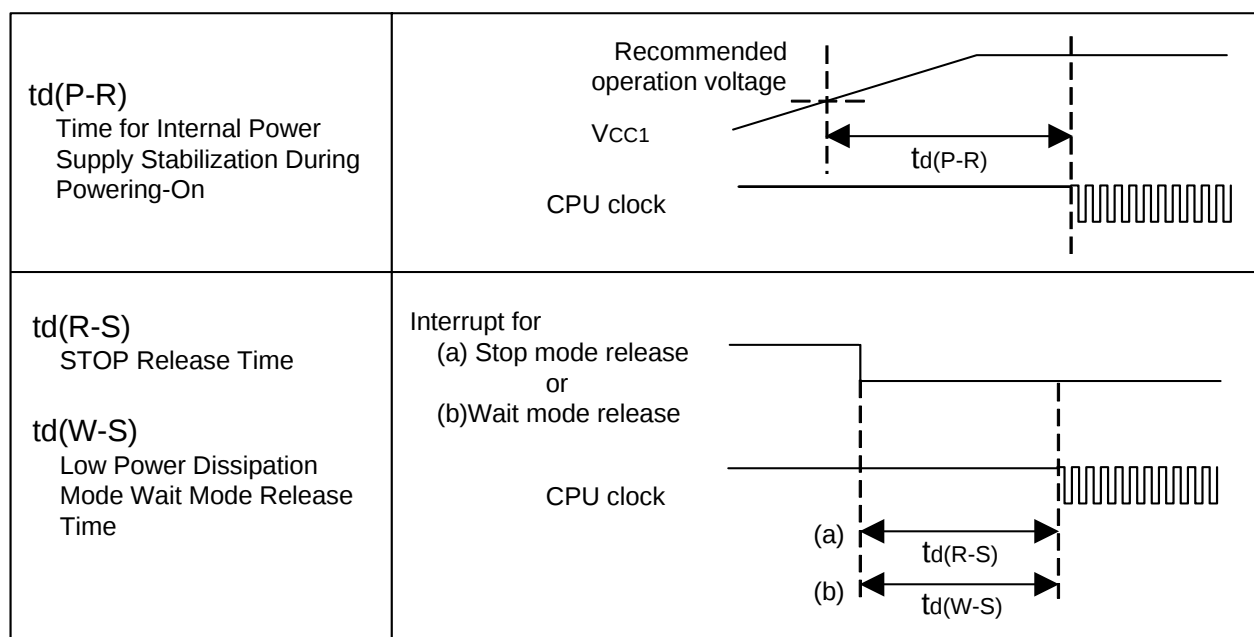
Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
Icc	Power Supply Current (Vcc1=Vcc2=2.7V to 3.6V)	In single-chip mode, the output pins are open and other pins are Vss	Mask ROM	f(BCLK)=10MHz No division		8	11	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=10MHz, No division		8	13	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, VCC1=3.0V		12		mA
			Flash Memory Erase	f(BCLK)=10MHz, VCC1=3.0V		22		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM ⁽³⁾		25		μA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM ⁽³⁾		25		μA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory ⁽³⁾		420		μA
				On-chip oscillation, Wait mode		45		μA
				Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode ⁽²⁾ , Oscillation capability High		6.0	
			f(BCLK)=32kHz Wait mode ⁽²⁾ , Oscillation capability Low			1.8		μA
			Stop mode Topr =25°C			0.7	3.0	μA
Idet4	Low Voltage Detection Dissipation Current ⁽⁴⁾					0.6	4	μA
Idet3	Reset Area Detection Dissipation Current ⁽⁴⁾					0.4	2	μA

NOTES:

1. Referenced to V_{CC1}=V_{CC2}=2.7 to 3.3V, V_{SS} = 0V at T_{opr} = -20 to 85°C / -40 to 85°C, f(BCLK)=10MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.
4. I_{det} is dissipation current when the following bit is set to "1" (detection circuit enabled).
I_{det4}: VC27 bit in the VCR2 register
I_{det3}: VC26 bit in the VCR2 register

Table 5.56 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	$V_{CC1}=4.0V$ to $5.5V$			2	ms
$t_{d(R-S)}$	STOP Release Time				150	μs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	μs

**Figure 5.22 Power Supply Circuit Timing Diagram**

$$V_{CC1}=V_{CC2}=5V$$

Timing Requirements

($V_{CC1} = V_{CC2} = 5V$, $V_{SS} = 0V$, at $T_{opr} = -40$ to $85^{\circ}C$ (T version) / -40 to $125^{\circ}C$ (V version) unless otherwise specified)

Table 5.59 External Clock Input (XIN input)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	62.5		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	25		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	25		ns
t_r	External Clock Rise Time		15	ns
t_f	External Clock Fall Time		15	ns

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